# Transportvia a Q uantum Shuttle 

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#### Abstract

W e investigate the e ect of quantisation of vibrationalm odes on a system in which the transport path is through a quantum dot $m$ ounted on a cantilever or spring such that tunnelling to and from the dot is $m$ odulated by the oscillation. W e consider here the im plications of quantum aspects of the motion. Peaks in the current voltage characteristic are observed which correspond to avoided level crossings in the eigenvalue spectrum. Transport occurs through processes in which phonons are created. This provides a path for dissipation of energy as well as a m echanism for driving the oscillator, thus $m$ aking it easier for electrons to tunnel onto and $o$ the dot and be ferried across the devige.


K ey words: nanotechnology; m esoscopics; quantum shuttle; NEMS
$R$ ecent advances in the fabrication of nanom echanicaldevices[1] are show ing a distinct trend tow ards system $s$ in which a quantum description is required not only for the electronic behaviour but also for the me chanical aspects. W e therefore consider a m odelnano \{ electro\{m echanicalsystem consisting ofa quantum dot attached to a spring or cantilever which $m$ oves betw een 2 contacts; thus acting as an electron shuttle ( $F$ ig.1). D evices of th is sort have previously been fabricated albeit $w$ ith classicalm echanical behaviour[2].


Fig.1.A quantum shuttle consisting of a dot on springs anked by 2 stationary dots attached to sem i\{ in nite leads.

In th is work we consider 2 m odels:
(i) a 3 dot model in which the m oveable dot is anked by 2 stationary dots. This is described by a tight\{binding $m$ odel[3].

[^0]\[

$$
\begin{aligned}
& V e^{\left(\hat{d}^{y}+\hat{d}\right)} \text { (jंihlj+ jhincj) } \\
& \left.V e^{\left[\left(\hat{d}^{y}+\hat{d}\right) \quad 2 x_{0}\right]} \text { (jंcihrj}+\dot{j} \text { rihc }\right] \text { ); }
\end{aligned}
$$
\]

where $\ddot{\text { ihhijare pro jection operators for the three }}$ electronic states and the vibrationalm ode, frequency !, is operated on by $\hat{d}$.
(ii) a scattering $m$ odelin $w$ hich the dot is em bedded betw een sem i\{ in nite leads in a Landauer[4] geom etry.

$$
\begin{align*}
& H= E e \frac{\varrho^{2}}{\varrho x_{e}^{2}} \quad E_{s} \frac{\varrho^{2}}{\varrho y_{s}}  \tag{2}\\
& \frac{1}{4} y_{s}^{2} \\
&+V_{1}\left[\begin{array}{lll}
\left(x_{e} ; d_{c}\right) & \left(x_{e}\right. & \left.\left.S y_{s} ; d_{s}\right)\right]
\end{array}\right.
\end{align*}
$$

where $x_{e}$ and $y_{s}$ represent the electron and phonon coordinates respectively, $E_{e}$ and $E_{s}$ the corresponding energy scales, $s$ the shuttle displacem ent,

$$
(x ; d)=\left(x_{e}+\frac{1}{2} d\right) \quad\left(x_{e} \quad \frac{1}{2} d\right)
$$

a barrier of $w$ idth $d ; d_{c}$ and $d_{s}$ represent the separation of the contacts and the size of the shuttle respectively.

The presence of the exponential term $s$ in (2) and a sim ilar term in them atching conditions of (3) $m$ ake the tunnelling rates sensitive to the position of the shuttle.


F ig.2.E igenvalues of the 3 \{dot m odelas a function of potential di erence betw een the outer dots; (a) w ithout tunnelling, (b) w ith tunnelling.

W hen the energies of the 3 dot system are plotted against the potentialdi erence betw een the outer dots the tunnelling through the shuttle results in a series of anti-crossings ( $F$ ig. 2). These are of 2 types: those involving only the outer dots, such as at $(1 ; 1)$ in 9.2 ; those involving all 3 dots, such as at $(2 ; 1: 5)$ in 9.2 .


F ig. 3. Current in the $3\{$ dot m odel as a function of potential di erence for 3 di erent dam ping rates (sh ifted for clarity).

The resulting current\{voltage characteristic is shown in g. 3. There is a peak at $\mathrm{b}=0$ due to resonant tunnelling through all 3 dots. $T$ he other features $m$ ay be associated $w$ th anti\{crossings in $g .2$. The maxim um at "b 0:8 occurs when the di erence betw een the energies of the left and right\{hand dots di er by that of a single phonon, whereas the peak at "b 2:0 involves 2 phonons and is associated $w$ ith a $3\{w a y$ anti\{crossing. $N$ ote, in particular, that the latter peak is $m u c h ~ m$ ore sensitive to the dam ping of the phonons than is the form er. T his is clearly due to the involvem ent of the state on the shuttle itself.

Results for the scattering m odel are illustrated in g.4.T he various curves corresp ond to di erent states of the shuttlebefore the electron is scattered. $N$ ote that the half\{ w idth of the peaks settles dow $n$ to about double the phonon energy, corresponding to a transm is-


Fig. 4. Total transm ission probability as a function of total energy (electron+ phonon) forvarious incident phonon num bers ( $\mathrm{n}=019$ start at $\mathrm{E}=\mathrm{n} / 10$ ). Shuttle displacem ent is zero (upper gure), about 40\% of the barrierw idth (lower gure). $T$ he on set of a 2 nd resonant tunnelling peak is seen to the right.
sion tim e of about half the shuttle period as w ould be expected for the shuttle e ect.

W e have presented results for 2 di erent $m$ odels of a quantum shuttle. In both cases there was no necessity to include a speci c m echanism to drive the shuttle. As long as the potential di erence across the system is greater than the phonon energy the shuttle $m$ ay be driven by the creation ofphonons. $T$ his in tum im plies that the dissipation of this energy willplay an im portant role in the behaviour of such a system.

## A cknow ledgem ents

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